
2SK2958(L),2SK2958(S)

Silicon N Channel MOS FET
High Speed Power Switching

HITACHI

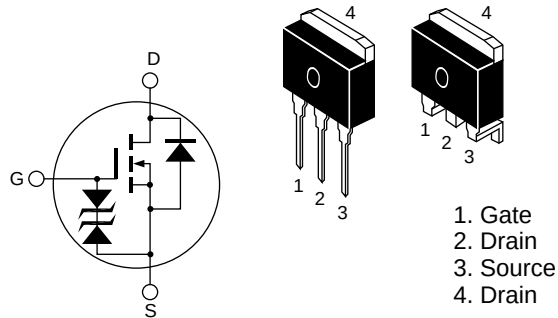
ADE-208-568B (Z)
3rd. Edition
June 1, 1998

Features

- Low on-resistance
 $R_{DS(on)} = 5.5m\Omega$ typ.
- 4V gate drive devices.
- High speed switching

Outline

LDPAK



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	30	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	75	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	300	A
Body-drain diode reverse drain current	I_{DR}	75	A
Channel dissipation	P_{ch} ^{Note2}	100	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

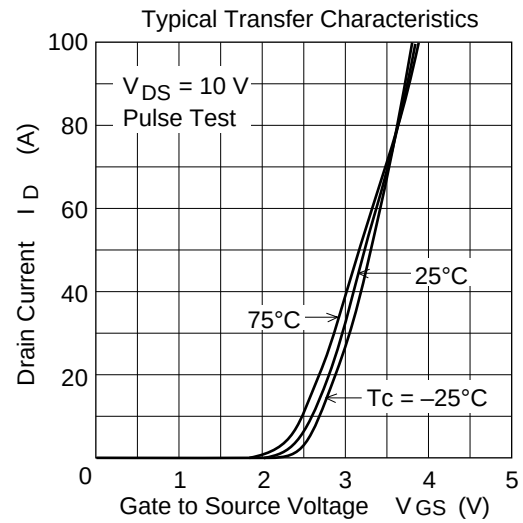
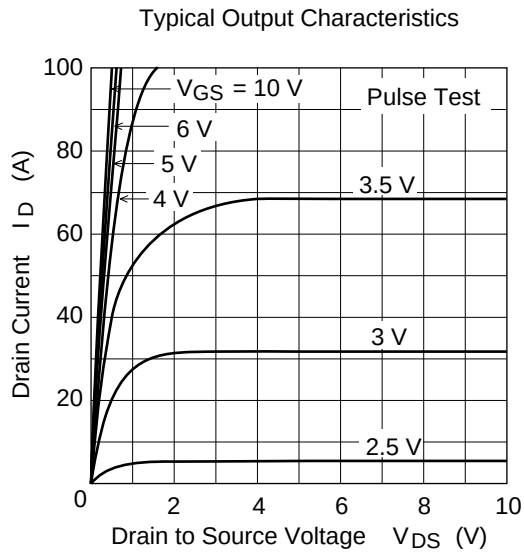
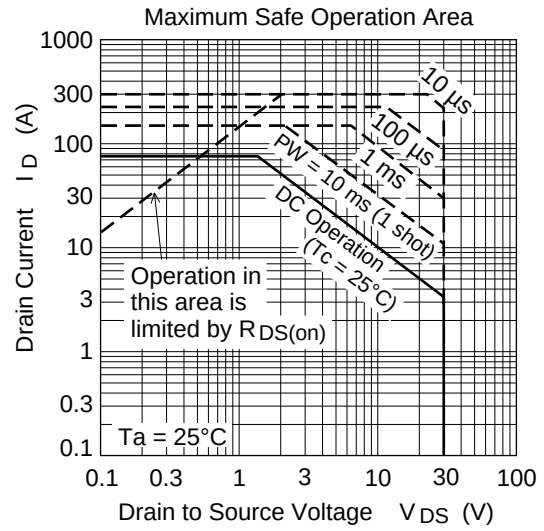
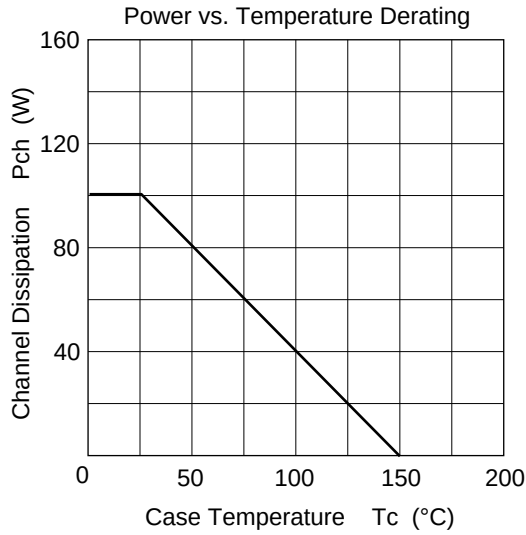
Note: 1. $PW \leq 10\mu s$, duty cycle $\leq 1\%$
2. Value at $T_c = 25^\circ C$

Electrical Characteristics (Ta = 25°C)

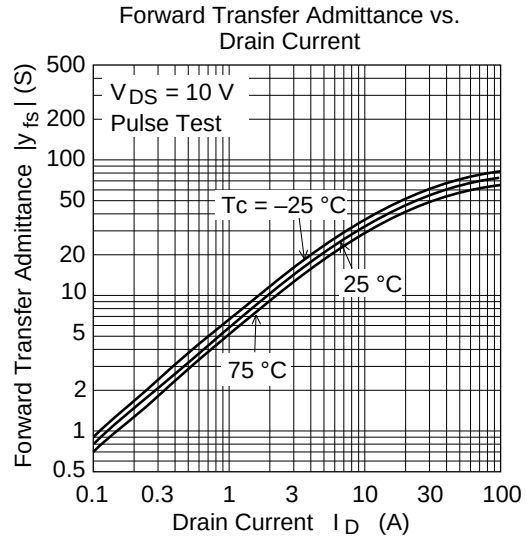
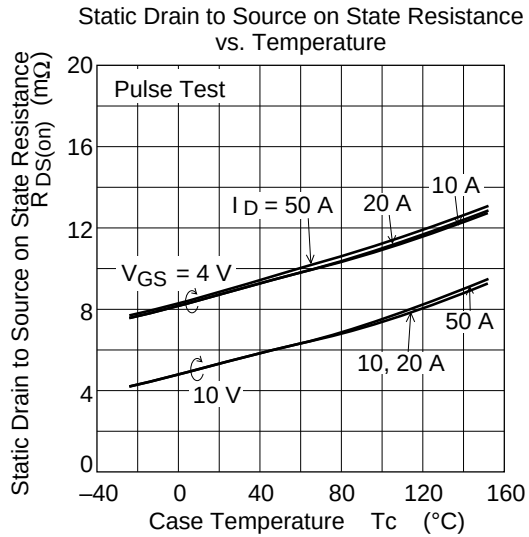
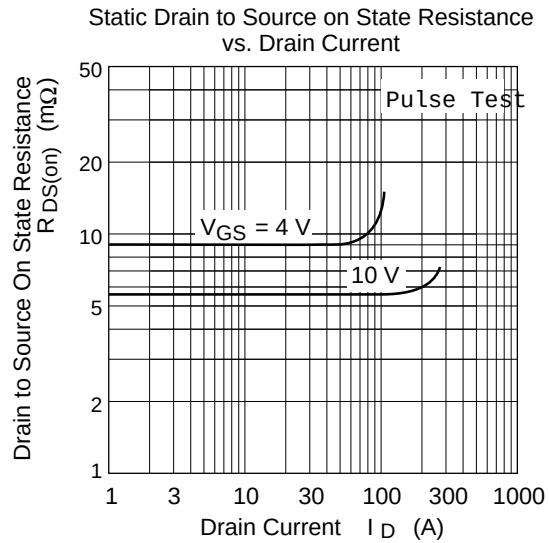
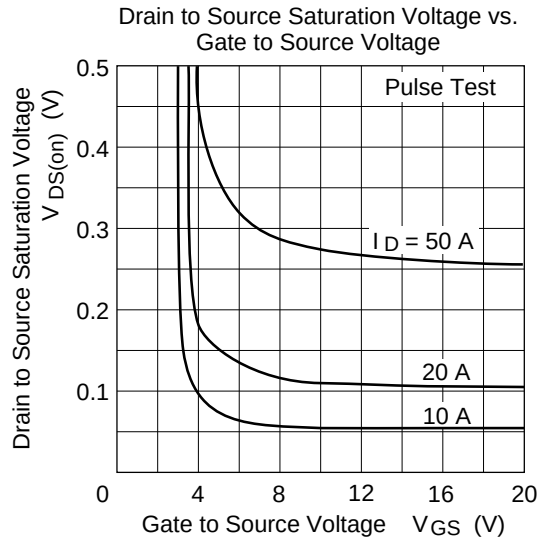
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30	—	—	V	$I_D = 10mA$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100\mu A$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 30V$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16V$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1mA$, $V_{DS} = 10V$
Static drain to source on state resistance	$R_{DS(on)}$	—	5.5	7.0	mΩ	$I_D = 40A$, $V_{GS} = 10V$ ^{Note3}
Static drain to source on state resistance	$R_{DS(on)}$	—	9.0	14.0	mΩ	$I_D = 40A$, $V_{GS} = 4V$ ^{Note3}
Forward transfer admittance	$ y_{fs} $	35	60	—	S	$I_D = 40A$, $V_{DS} = 10V$ ^{Note3}
Input capacitance	C_{iss}	—	4100	—	pF	$V_{DS} = 10V$
Output capacitance	C_{oss}	—	2700	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	800	—	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}$	—	45	—	ns	$V_{GS} = 10V$, $I_D = 40A$
Rise time	t_r	—	430	—	ns	$R_L = 0.25\Omega$
Turn-off delay time	$t_{d(off)}$	—	460	—	ns	
Fall time	t_f	—	440	—	ns	
Body-drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 75A$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	90	—	ns	$I_F = 75A$, $V_{GS} = 0$ $diF/dt = 50A/\mu s$

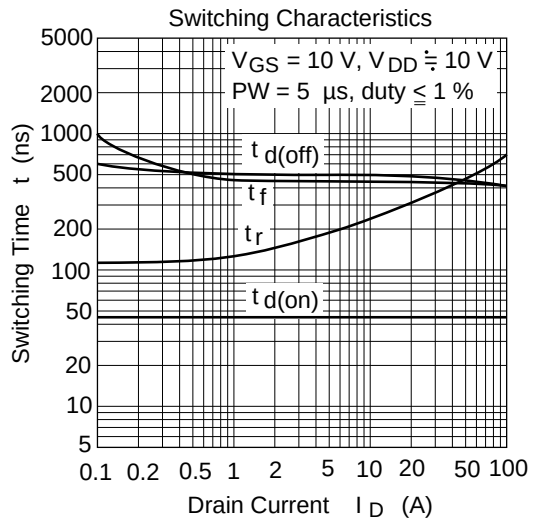
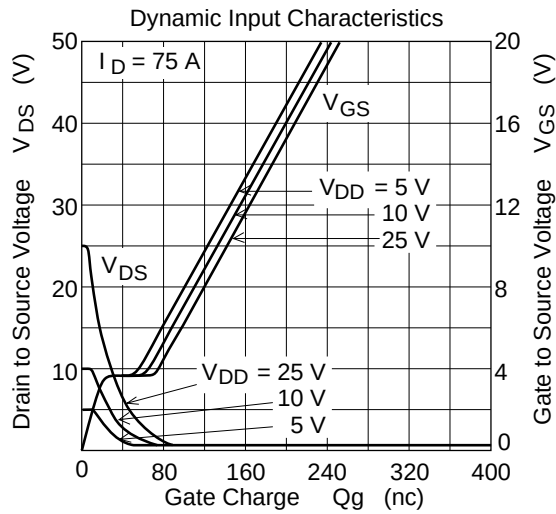
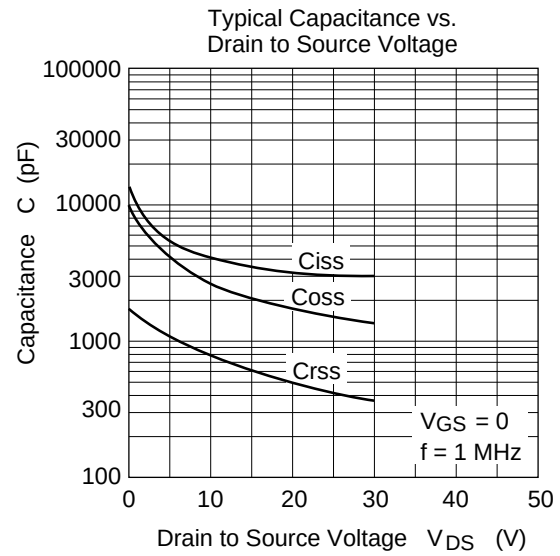
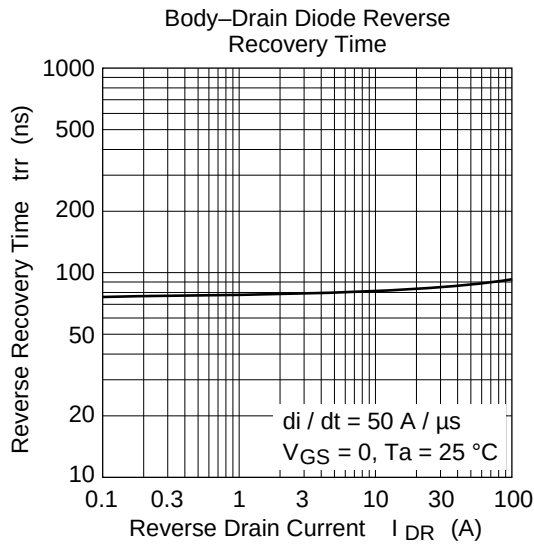
Note: 3. Pulse test

Main Characteristics

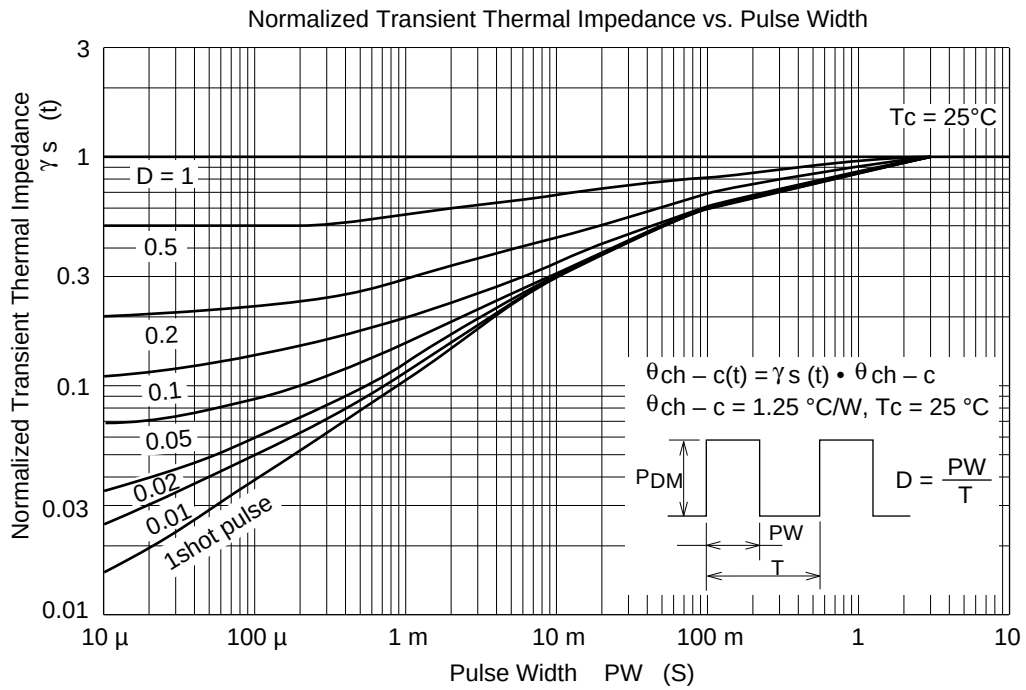
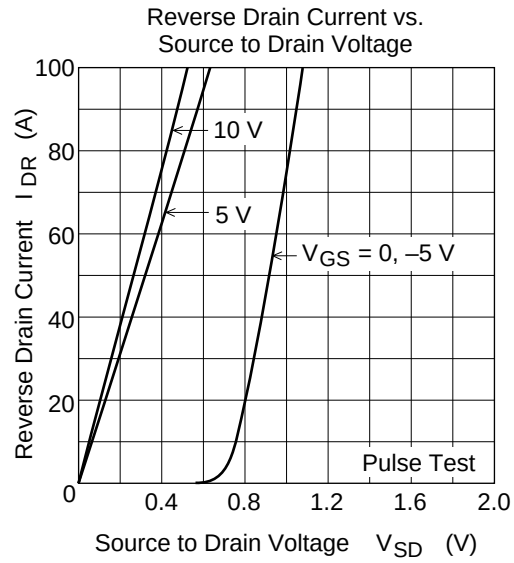


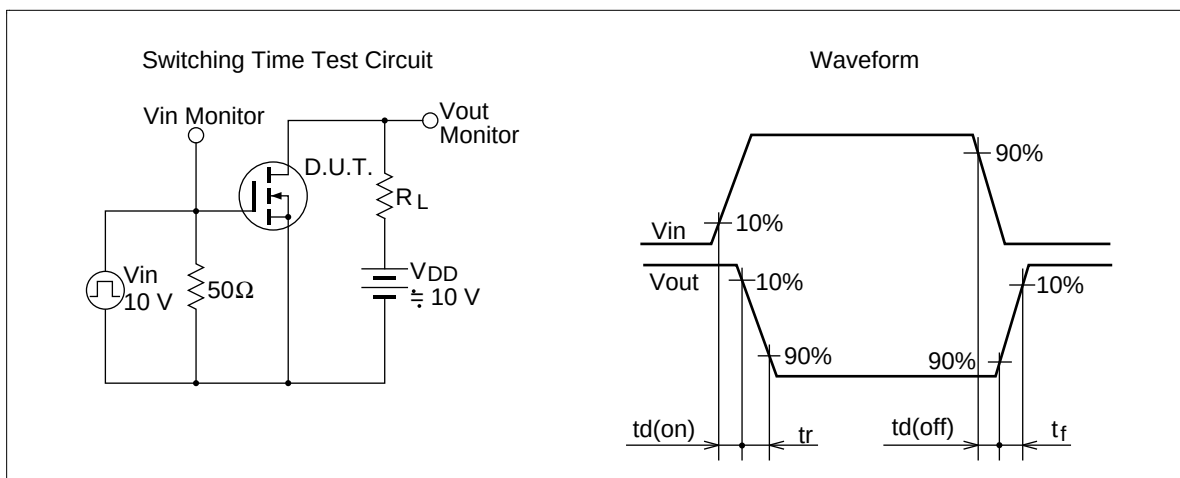
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